
2SA1188, 2SA1189

Silicon PNP Epitaxial

HITACHI

Application

- Low frequency amplifier
- Complementary pair with 2SC2853 and 2SC2854

Outline

TO-92 (1)



1. Emitter
2. Collector
3. Base

2SA1188, 2SA1189

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	2SA1188	2SA1189	Unit
Collector to base voltage	V_{CBO}	-90	-120	V
Collector to emitter voltage	V_{CEO}	-90	-120	V
Emitter to base voltage	V_{EBO}	-5	-5	V
Collector current	I_C	-100	-100	mA
Emitter current	I_E	100	100	mA
Collector power dissipation	P_C	400	400	mW
Junction temperature	T_j	150	150	°C
Storage temperature	T_{stg}	-55 to +150	-55 to +150	°C

Electrical Characteristics (Ta = 25°C)

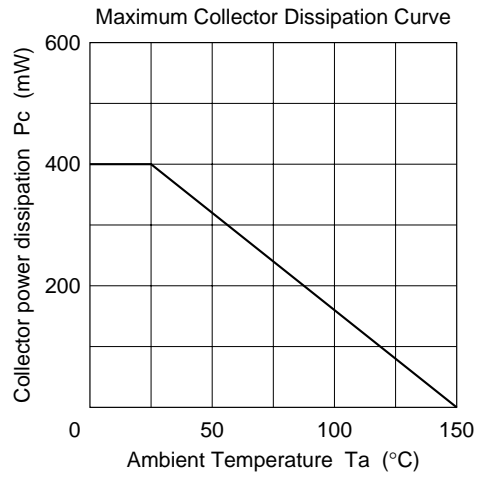
Item	Symbol	2SA1188			2SA1189			Unit	Test conditions
		Min	Typ	Max	Min	Typ	Max		
Collector to base breakdown voltage	$V_{(BR)CBO}$	-90	—	—	-120	—	—	V	$I_C = -10 \mu A, I_E = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	-90	—	—	-120	—	—	V	$I_C = -1 \text{ mA}, R_{BE} = \infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	-5	—	—	-5	—	—	V	$I_E = -10 \mu A, I_C = 0$
Collector cutoff current	I_{CBO}	—	—	-0.1	—	—	-0.1	μA	$V_{CB} = -70 \text{ V}, I_E = 0$
Emitter cutoff current	I_{EBO}	—	—	-0.1	—	—	-0.1	μA	$V_{EB} = -2 \text{ V}, I_C = 0$
DC current transfer ratio	h_{FE}^{*1}	250	—	800	250	—	800		$V_{CE} = -12 \text{ V}, I_C = -2 \text{ mA}^{*2}$
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	-0.05	-0.15	—	-0.05	-0.15	V	$I_C = -10 \text{ mA}, I_B = -1 \text{ mA}^{*2}$
Base to emitter saturation voltage	$V_{BE(sat)}$	—	-0.7	-1.0	—	-0.7	-1.0	V	
Gain bandwidth product	f_T	—	130	—	—	130	—	MHz	$V_{CE} = -6 \text{ V}, I_C = -10 \text{ mA}$
Collector output capacitance	C_{ob}	—	3.2	—	—	3.2	—	pF	$V_{CB} = -10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$

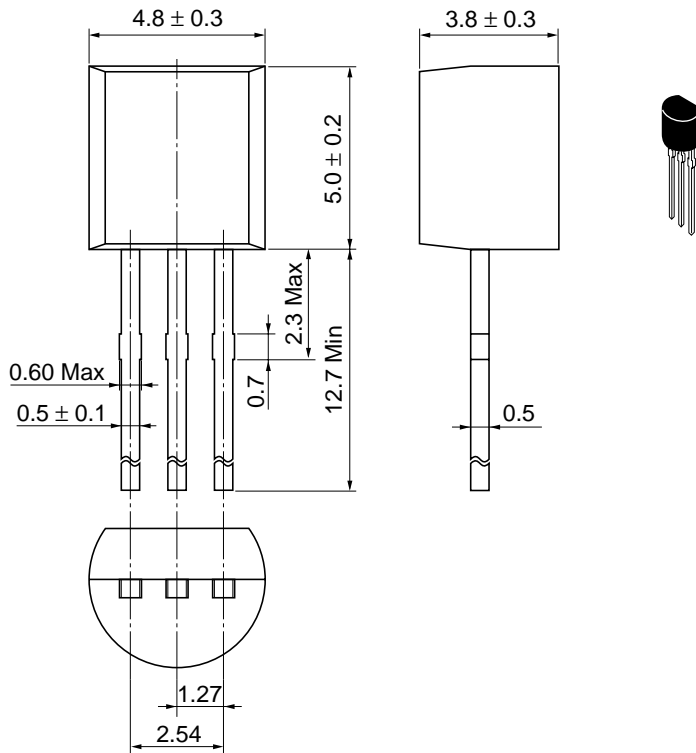
Notes: 1. The 2SA1188 and 2SA1189 are grouped by h_{FE} as follows.

2. Pulse test

D	E
250 to 500	400 to 800

See characteristic curves of 2SA1190 and 2SA1191.





Hitachi Code	TO-92 (1)
JEDEC	Conforms
EIAJ	Conforms
Weight (reference value)	0.25 g

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Hitachi, Ltd.

Semiconductor & Integrated Circuits.
Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan
Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

URL North America : <http://semiconductor.hitachi.com/>
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For further information write to:

Hitachi Semiconductor
(America) Inc.
179 East Tasman Drive,
San Jose, CA 95134
Tel: <1> (408) 433-1990
Fax: <1> (408) 433-0223

Hitachi Europe GmbH
Electronic components Group
Dornacher Straße 3
D-85622 Feldkirchen, Munich
Germany
Tel: <49> (89) 9 9180-0
Fax: <49> (89) 9 29 30 00

Hitachi Europe Ltd.
Electronic Components Group.
Whitebrook Park
Lower Cookham Road
Maidenhead
Berkshire SL6 8YA, United Kingdom
Tel: <44> (1628) 585000
Fax: <44> (1628) 778322

Hitachi Asia Pte. Ltd.
16 Collyer Quay #20-00
Hitachi Tower
Singapore 049318
Tel: 535-2100
Fax: 535-1533

Hitachi Asia Ltd.
Taipei Branch Office
3F, Hung Kuo Building, No.167,
Tun-Hwa North Road, Taipei (105)
Tel: <886> (2) 2718-3666
Fax: <886> (2) 2718-8180

Hitachi Asia (Hong Kong) Ltd.
Group III (Electronic Components)
7/F., North Tower, World Finance Centre,
Harbour City, Canton Road, Tsim Sha Tsui,
Kowloon, Hong Kong
Tel: <852> (2) 735 9218
Fax: <852> (2) 730 0281
Telex: 40815 HITEC HX

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